PROCESS CP287

Power Transistor

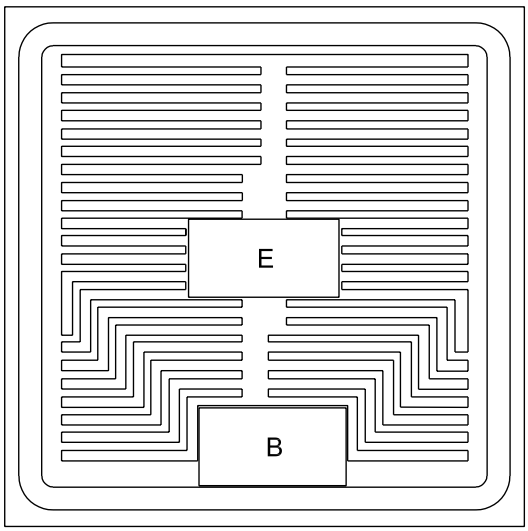
8.0 Amp NPN Silicon Power Transistor Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Die Size	130 x 130 MILS
Die Thickness	9.5 MILS
Base Bonding Pad Area	37 x 20 MILS
Emitter Bonding Pad Area	38 x 20 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Ti/Ni/Ag - (3000Å, 10,000Å, 10,000Å)

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

974

PRINCIPAL DEVICE TYPES

MJE13007

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R0 (26-July 2005)